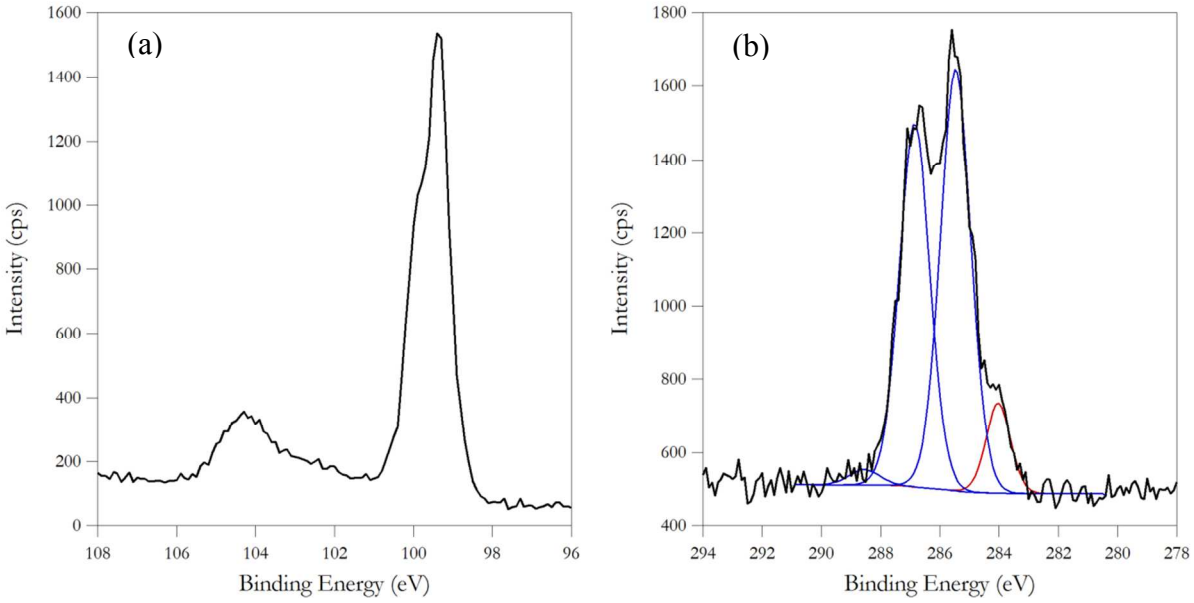
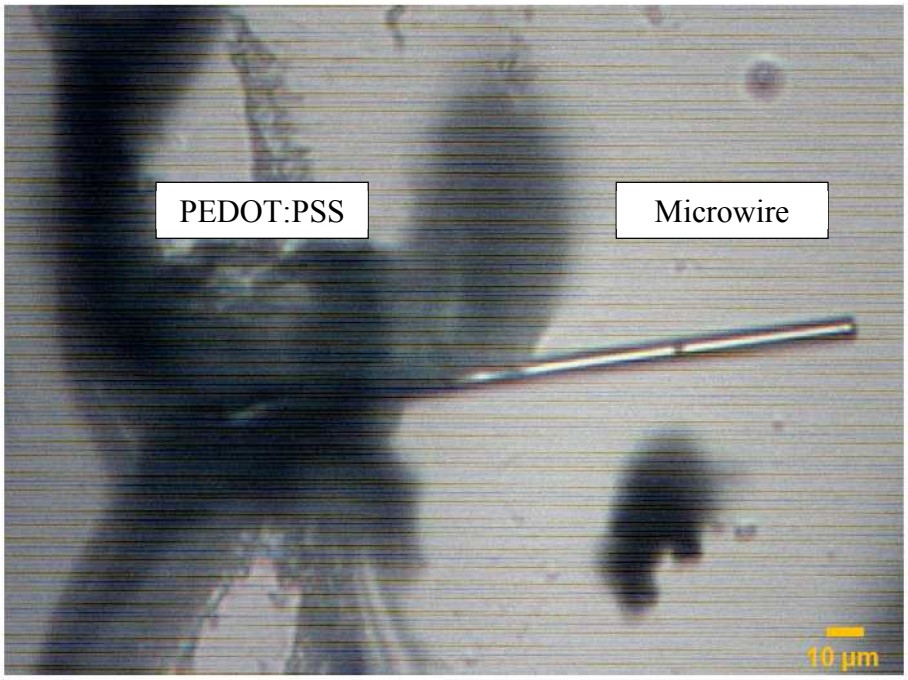


SI 1. High resolution X-ray photoelectron spectra of n^+ Si microwire array (a) Si 2p region. The peak at 104 eV is characteristic of thick (~500nm) silicon oxide layer located at the base of microwire arrays. (b) C 1s region. Peak at 284 eV is characteristic of C-Si bond.



SI 2. Microwire contact to PEDOT:PSS. Entire contacting surface of Si microwire is embedded in PEDOT:PSS forming intimate contact.